C3D10060A
Silicon Carbide Schottky Diode
Z-Rec® RECTIFIER

Features
• 600-Volt Schottky Rectifier
• Zero Reverse Recovery Current
• Zero Forward Recovery Voltage
• High-Frequency Operation
• Temperature-Independent Switching Behavior
• Extremely Fast Switching
• Positive Temperature Coefficient on \( V_F \)

Benefits
• Replace Bipolar with Unipolar Rectifiers
• Essentially No Switching Losses
• Higher Efficiency
• Reduction of Heat Sink Requirements
• Parallel Devices Without Thermal Runaway

Applications
• Switch Mode Power Supplies (SMPS)
• Boost diodes in PFC or DC/DC stages
• Free Wheeling Diodes in Inverter stages
• AC/DC converters

Maximum Ratings (\( T_c = 25 \degree C \) unless otherwise specified)

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Value</th>
<th>Unit</th>
<th>Test Conditions</th>
<th>Note</th>
</tr>
</thead>
<tbody>
<tr>
<td>( V_{RRM} )</td>
<td>Repetitive Peak Reverse Voltage</td>
<td>600</td>
<td>V</td>
<td></td>
<td></td>
</tr>
<tr>
<td>( V_{RSM} )</td>
<td>Surge Peak Reverse Voltage</td>
<td>600</td>
<td>V</td>
<td></td>
<td></td>
</tr>
<tr>
<td>( V_{DC} )</td>
<td>DC Blocking Voltage</td>
<td>600</td>
<td>V</td>
<td></td>
<td></td>
</tr>
<tr>
<td>( I_F )</td>
<td>Continuous Forward Current</td>
<td>30</td>
<td>A</td>
<td>( T_c=25\degree C ) ( T_{stg}=135\degree C ) ( T_{stg}=153\degree C )</td>
<td>Fig. 3</td>
</tr>
<tr>
<td>( I_{FRM} )</td>
<td>Repetitive Peak Forward Surge Current</td>
<td>46</td>
<td>A</td>
<td>( T_c=25\degree C, t_p=10) ms, Half Sine Wave ( T_{stg}=110\degree C, t_p=10) ms, Half Sine Wave</td>
<td></td>
</tr>
<tr>
<td>( I_{FSM} )</td>
<td>Non-Repetitive Peak Forward Surge Current</td>
<td>90</td>
<td>A</td>
<td>( T_c=25\degree C, t_p=10) ms, Half Sine Wave ( T_{stg}=110\degree C, t_p=10) ms, Half Sine Wave</td>
<td>Fig. 8</td>
</tr>
<tr>
<td>( I_{F,Max} )</td>
<td>Non-Repetitive Peak Forward Surge Current</td>
<td>860</td>
<td>A</td>
<td>( T_c=25\degree C, t_p=10) µs, Pulse ( T_{stg}=110\degree C, t_p=10) µs, Pulse</td>
<td>Fig. 8</td>
</tr>
<tr>
<td>( P_{tot} )</td>
<td>Power Dissipation</td>
<td>136.5</td>
<td>W</td>
<td>( T_c=25\degree C ) ( T_{stg}=110\degree C )</td>
<td>Fig. 4</td>
</tr>
<tr>
<td>( T_J, T_{stg} )</td>
<td>Operating Junction and Storage Temperature</td>
<td>-55 to +175</td>
<td>°C</td>
<td></td>
<td></td>
</tr>
<tr>
<td>( \text{TO-220 Mounting Torque} )</td>
<td></td>
<td>1</td>
<td>Nm</td>
<td>\text{M3 Screw}</td>
<td></td>
</tr>
</tbody>
</table>

\( V_{RRM} = 600 \text{ V} \)
\( I_F(T_c=135\degree C) = 14.5 \text{ A} \)
\( Q_c = 24 \text{ nC} \)
### Electrical Characteristics

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Typ.</th>
<th>Max.</th>
<th>Unit</th>
<th>Test Conditions</th>
<th>Note</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_F$</td>
<td>Forward Voltage</td>
<td>1.5</td>
<td>1.8</td>
<td>V</td>
<td>$I_F = 10\ A, T_J = 25\ ^\circ C$</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>2.0</td>
<td>2.4</td>
<td></td>
<td>$I_F = 10\ A, T_J = 175\ ^\circ C$</td>
<td>Fig. 1</td>
</tr>
<tr>
<td>$I_R$</td>
<td>Reverse Current</td>
<td>10</td>
<td>50</td>
<td>$\mu A$</td>
<td>$V_R = 600\ V, T_J = 25\ ^\circ C$</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>20</td>
<td>200</td>
<td></td>
<td>$V_R = 600\ V, T_J = 175\ ^\circ C$</td>
<td>Fig. 2</td>
</tr>
<tr>
<td>$Q_C$</td>
<td>Total Capacitive Charge</td>
<td>24</td>
<td></td>
<td>nC</td>
<td>$V_R = 600\ V, I_F = 10\ A$</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>$dI/dt = 500\ A/\mu s, T_J = 25\ ^\circ C$</td>
<td>Fig. 5</td>
</tr>
<tr>
<td>$C$</td>
<td>Total Capacitance</td>
<td>460.5</td>
<td>44</td>
<td>pF</td>
<td>$V_R = 400\ V, I_F = 10\ A$</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>40</td>
<td></td>
<td></td>
<td>$T_J = 25\ ^\circ C, f = 1\ MHz$</td>
<td></td>
</tr>
<tr>
<td>$E_C$</td>
<td>Capacitance Stored Energy</td>
<td>3.6</td>
<td></td>
<td>$\mu J$</td>
<td>$V_R = 400\ V$</td>
<td></td>
</tr>
</tbody>
</table>

Note: This is a majority carrier diode, so there is no reverse recovery charge.

### Thermal Characteristics

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Typ.</th>
<th>Unit</th>
<th>Note</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_{JC}$</td>
<td>Thermal Resistance from Junction to Case</td>
<td>1.1</td>
<td>°C/W</td>
<td>Fig. 9</td>
</tr>
</tbody>
</table>

### Typical Performance

![Figure 1. Forward Characteristics](image1)

![Figure 2. Reverse Characteristics](image2)
Typical Performance

Figure 3. Current Derating

Figure 4. Power Derating

Figure 5. Total Capacitance Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

Conditions:
- \( T_j = 25 \degree C \)
- \( F_{test} = 1 \text{ MHz} \)
- \( V_{test} = 25 \text{ mV} \)
Typical Performance

Figure 7. Capacitance Stored Energy

Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

Figure 9. Transient Thermal Impedance
Package Dimensions

POS | Inches | Millimeters
--- | -------| -----------
A | .381 - .410 | 9.677 - 10.414
B | .235 - .255 | 5.969 - 6.477
C | .100 - .120 | 2.540 - 3.048
D | .223 - .337 | 5.664 - 8.560
D1 | .457-490 | 11.60-12.45 typ
D2 | .277-.303 typ | 7.04-7.70 typ
D3 | .244-.252 typ | 6.22-6.4 typ
E | .590 - .615 | 14.986 - 15.621
E1 | .302 - .326 | 7.68 - 8.28
E2 | .227 - .251 | 5.77 - 6.37
F | .143 - .153 | 3.632 - 3.886
G | 1.105 - 1.147 | 28.067 - 29.134
H | .500 - .550 | 12.700 - 13.970
L | .025 - .036 | .635 - .914
M | .045 - .055 | 1.143 - 1.550
N | .195 - .205 | 4.953 - 5.207
P | .165 - .185 | 4.191 - 4.699
Q | .048 - .054 | 1.219 - 1.372
S | 3° - 6° | 3° - 6°
T | 3° - 6° | 3° - 6°
U | 3° - 6° | 3° - 6°
V | .094 - .110 | 2.388 - 2.794
W | .014 - .025 | .356 - .635
X | .385 - .410 | 9.779 - 10.414
Y | .130 - .150 | 3.302 - 3.810

NOTE:
1. Dimension L, M, W apply for Solder Dip Finish

Recommended Solder Pad Layout

Part Number | Package | Marking
--- | -------| ---
C3D10060A | TO-220-2 | C3D10060

Note: Recommended soldering profiles can be found in the applications note here: [http://www.wolfspeed.com/power_app_notes/soldering](http://www.wolfspeed.com/power_app_notes/soldering)
Diode Model

\[
V_f = V_T + I_f R_T
\]

\[
V_T = 0.94 + (T_J \times 1.3 \times 10^{-3})
\]

\[
R_T = 0.044 + (T_J \times 4.4 \times 10^{-4})
\]

Note: \( T_J \) = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

Notes

- **RoHS Compliance**
  The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Ecology section of our website at http://www.wolfspeed.com/Power/Tools-and-Support/Product-Ecology.

- **REACH Compliance**
  REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: http://www.wolfspeed.com/diodes
- SiC MOSFET and diode reference designs: http://go.pardot.com/l/101562/2015-07-31/349i